

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device has an active layer, a first cladding layer formed on the active layer, and a second cladding layer formed on the first cladding layer. The first cladding layer is doped with magnesium as a first impurity to have a high resistivity. The 5 second cladding layer is doped with zinc as a second impurity to have a resistivity lower than the resistivity of the first cladding layer.